

4. The method according to any one of claims 1 to 3, further comprising forming a recess in the carrier (7) for insertion of the connecting means(10).

5. The method according to any one of claims 1 to 3, wherein the one side (1) of the wafer (W) is partially cut by laser and a further area of the wafer is cut mechanically.

6. The method according to claim 5, wherein the further area of the wafer (W) is cut mechanically from the one side (1) of the wafer (W) or from the side (6) of the wafer (W) being opposite to the one side (1).

10

7. The method according to any one of claims 1 to 3, wherein the side (6) of the wafer (W) being opposite to the one side (1) is mechanically partially cut and a further area of the wafer (W) is cut by laser from the side (6) of the wafer (W) being opposite to the one side (1).

15 8. The method according to any one of claims 1 to 3, wherein the cutting of the wafer is performed before grinding of the wafer.

9. The method according claim 1, wherein the steps of claim 1 are performed in the listed order.

20 10. The method according to any one of claims 1 to 3, wherein the surface of the adhesive tape (4) opposite the surface contacting the devices is parallelized with the surface of the wafer (W) opposite the one side (1).

11. The method according any one of claims 1 to 3, further comprising
25 attaching an adhesive pick up tape (11) to the ground surface of the wafer (W).

12. The method according to any one of claims 1 to 3, wherein the carrier (7) is made of silicon, glass, or both.